

/ Descriptions

SOP-8 N MOS

N-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

/ Features

$V_{DS}(V)=30V$ $I_D=6.9A$

$R_{DS(ON)} < 32m$ ($V_{GS}=10V$)

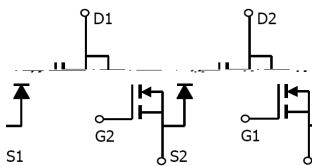
$R_{DS(ON)} < 36m$ ($V_{GS}=4.5V$)

$R_{DS(ON)} < 52m$ ($V_{GS}=2.5V$)

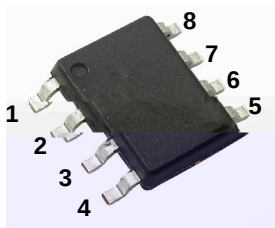
/ Applications

Power Management in Notebook computer, Portable Equipment and Battery powered systems and this device is suitable for use as a load switch or in PWM applications.

/ Equivalent Circuit



/ Pinning



PIN1	S2	PIN 2	G2	PIN 3	S1	PIN 4	G1
PIN 5	D1	PIN 6	D1	PIN 7	D2	PIN 8	D2

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25 °C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	$I_D (T_a=25^\circ\text{C})$	6.9	A
	$I_D (T_a=70^\circ\text{C})$	5.8	A
Pulsed Drain Current ^B	I_{DM}	40	A
Power Dissipation for Single Operation ^A	$P_D (T_a=25^\circ\text{C})$	2.0	W
	$P_D (T_a=70^\circ\text{C})$	1.44	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C
Thermal Resistance-Junction to Ambient ^A	$R_{JA} \quad t \leq 10s$	62.5	°C/W
	R_{JA}	110	°C/W
Maximum Junction-to-Lead ^C	R_{JL}	40	°C/W

Note:

A: The value of R_{JA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The R_{JA} is the sum of the thermal impedance from junction to lead R_{JL} and lead to ambient.

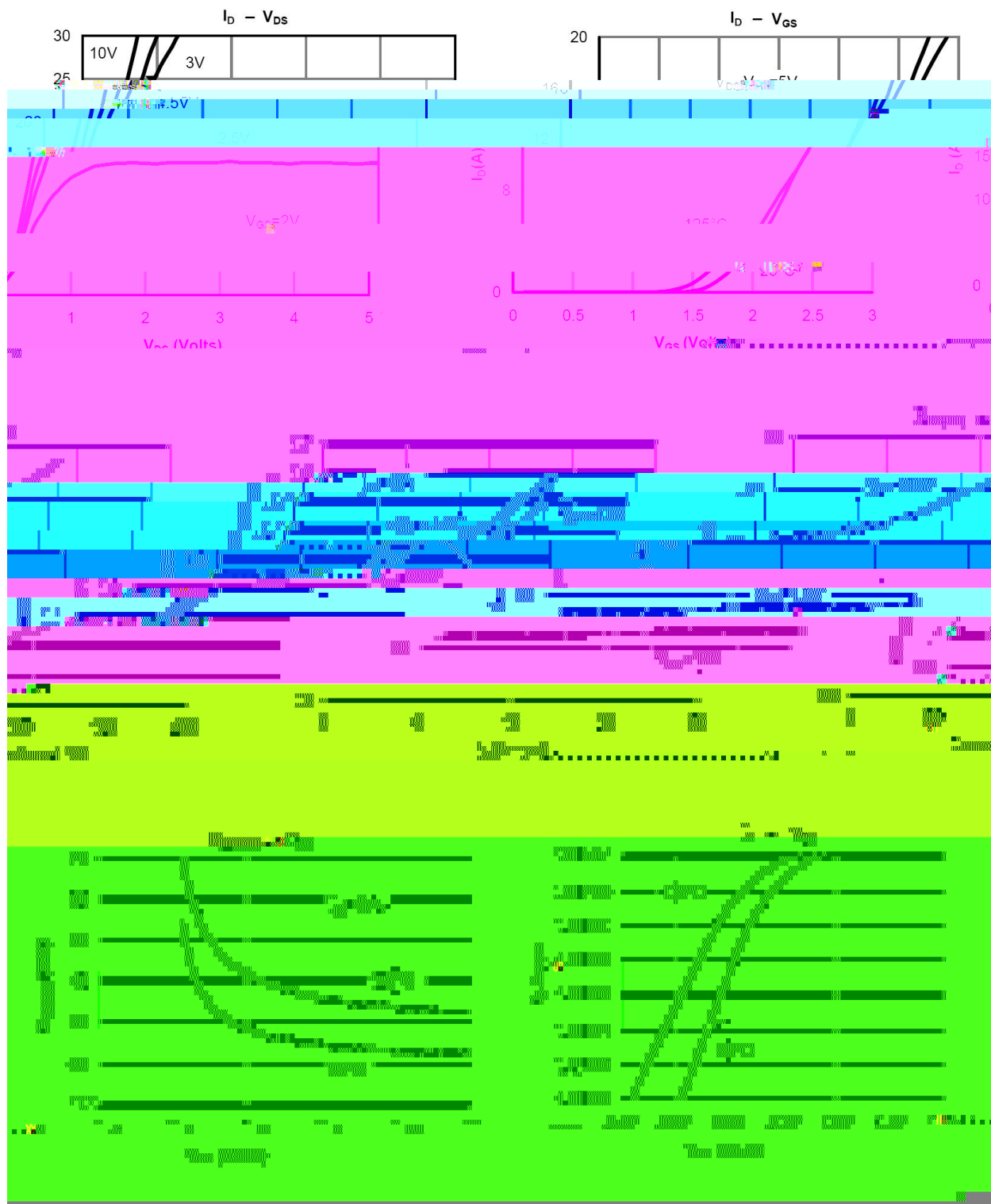
D. The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

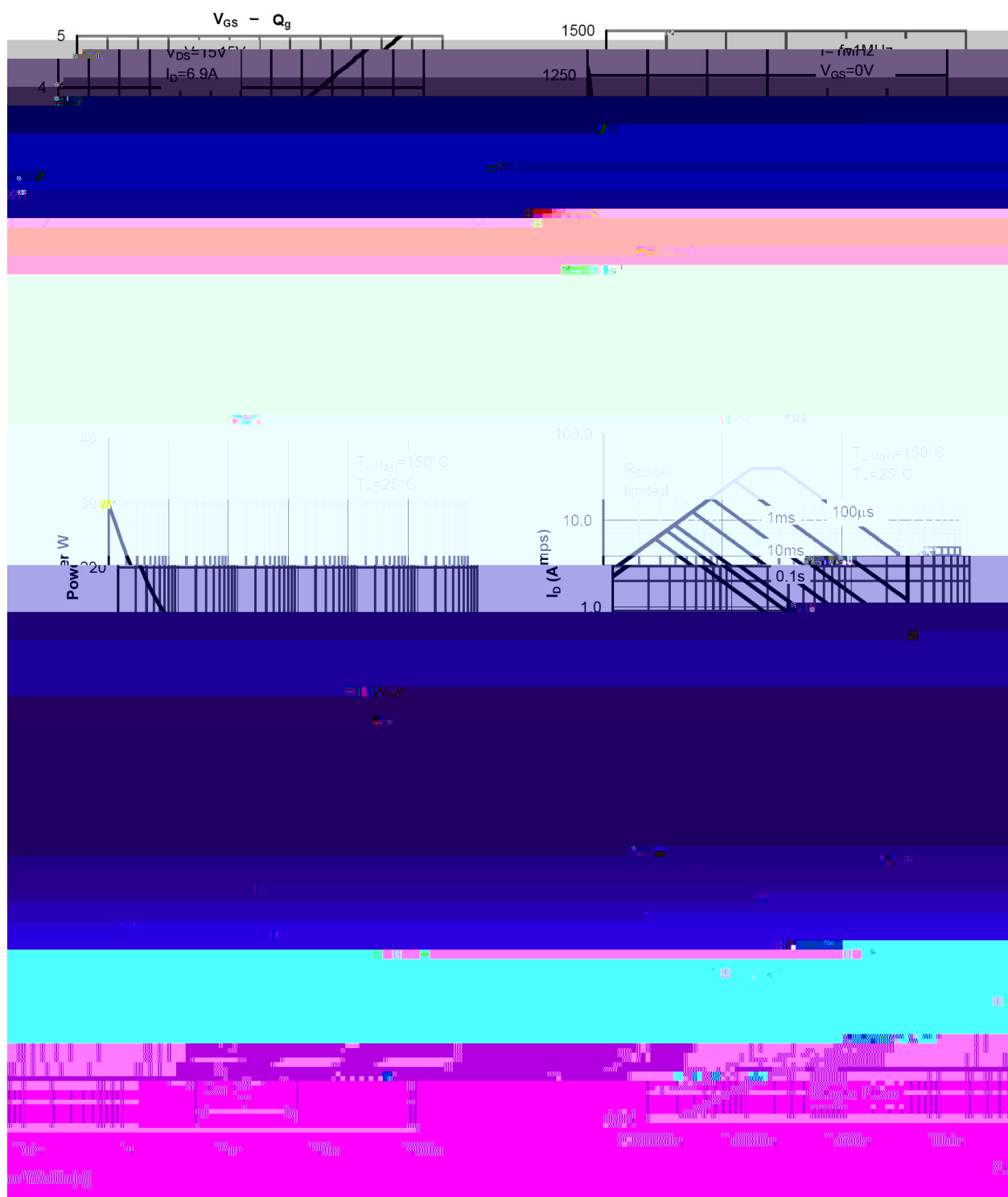
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\text{ A}$ $V_{GS}=0V$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V$ $V_{GS}=0V$			1.0	A
		$V_{DS}=24V$ $V_{GS}=0V$ $T_J=55^\circ C$			5.0	
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V$ $V_{GS}=\pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\text{ A}$	0.7	1.1	1.4	V
On state drain current	$I_{D(ON)}$	$V_{GS}=4.5V$ $V_{DS}=5.0V$	6.9			A
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V$ $I_D=6.9A$		24	32	m
		$V_{GS}=10V$ $I_D=6.9A$ $T_J=125^\circ C$		32.3	38	
		$V_{GS}=4.5V$ $I_D=6.0A$		27	36	
		$V_{GS}=2.5V$ $I_D=5.0A$		40	52	
Forward Transconductance	g_{FS}	$V_{DS}=5.0V$ $I_D=5.0A$	10	15		S
Diode Forward Voltage	V_{SD}	$I_S=1.0A$		0.77	1.0	V
Maximum Body-Diode Continuous Current	I_S				3.0	A
Total Gate Charge	Q_g	$V_{GS}=4.5V$ $V_{DS}=15V$ $I_D=6.9A$		9.6		nC
Gate-Source Charge	Q_{gs}			1.65		
Gate-Drain Charge	Q_{gd}			3.0		
Gate Resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		1.24		
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=15V$ $f=1MHz$		858		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{rss}			80		
Turn-on Delay Time	$t_{d(ON)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=2.2$ $R_{GEN}=6.0$		5.7		ns
Turn-on Rise Time	t_r			13		
Turn-off Delay Time	$t_{d(OFF)}$			37		
Turn-off Fall Time	t_f			4.2		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=5.0A$ $dI/dt=100A/s$		15.5		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=5.0A$ $dI/dt=100A/s$		7.9		nC

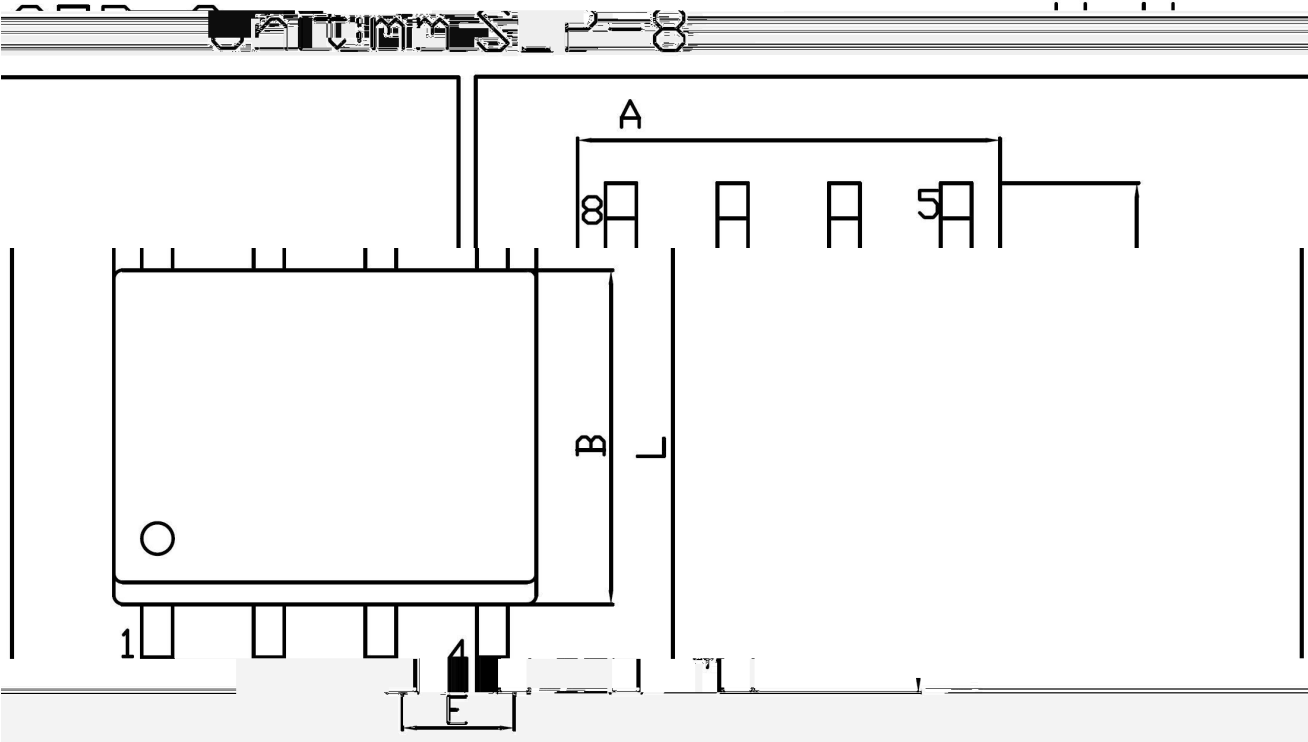
/ Electrical Characteristic Curve



Electrical Characteristic Curve

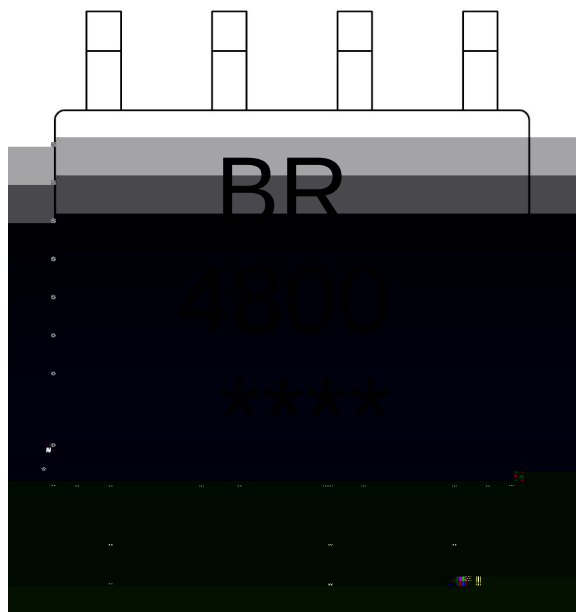


/ Package Dimensions



Dimensions In Millimeters				Dimensions In Millimeters			
Min.	Max.	Symbol	Min.	Max.	Symbol	Min.	Max.
4.170	5.510	C	1.305	1.755	A		
3.700	4.100	D	0.25	0.45	B		
L		5.80	6.20	R		0.30	0.60
E		1.27BSC		P		0°	7°
K		1.25	0.25	h		0.30	1.25

/ Marking Instructions



BR

4800

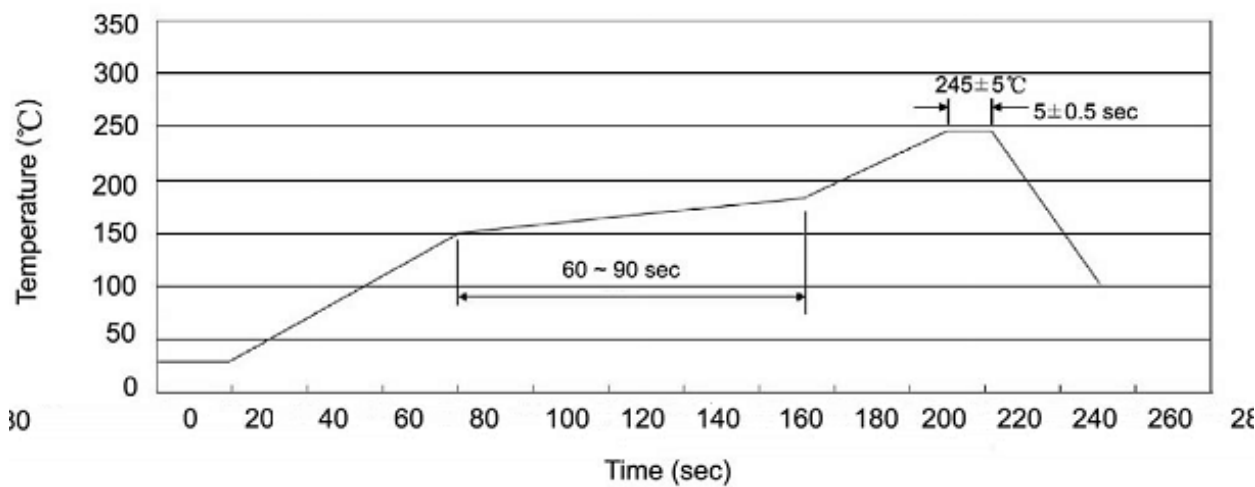
Note:

BR: Company Code.

4800: Product Type

****: Lot No. Code, code change with Lot No.

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Note:

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|---|-------|-----|-----------|--------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm ³)

/ Notices